

N-Channel 60-V (D-S) MOSFET

Features

- Low rDS(on) trench technology
- Low thermal impedance
- Fast switching speed
- Low thermal impedance copper lead frame DFN5X6-8L saves board space
- RoHS compliant package

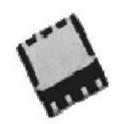
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Package type: DFN5X6-8L

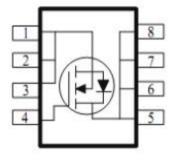
Packing & Order Information

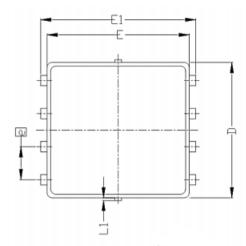
3,000/Reel

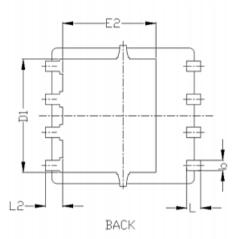


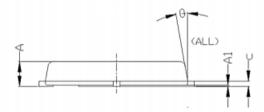
RoHS COMPLIANT

Graphic symbol









SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00	_	0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012 0.016	0.016	0.020	
С	0. 15	0.20	0.25	0.006	0.008	0.010	
D	5, 20 BSC			0, 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
Ll	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0° 10°			



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T _A =25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
V_{DS}	Drain-Source Voltage	60	V		
V_{GS}	Gate-Source Voltage	±20	V		
I_D	Continuous Drain Current ^a (T _A =25°C)	13	A		
	Continuous Drain Current ^a (T _A =70°C)	11	A		
I_{DM}	Pulsed Drain Current ^b	50	A		
Is	Continuous Source Current (Diode Conduction) ^a	4.6	A		
PD	Power Dissipation ^a (T _A =25°C)	5	W		
	Power Dissipation ^a (T _A =70°C)	3.2	W		
T _J /T _{STG}	Operating Junction and Storage Temperature	-55 to +150	°C		

Thermal Resistance Ratings					
Symbol	Parameter	Maximum	Units		
RөJA	Maximum Junction-to-Ambient ^a (t <= 10 sec)	25	°C/W		
	Maximum Junction-to-Ambient ^a (Steady-State)	65	C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{DS}=V_{GS},I_D\!=\text{-250}\mu\text{A}$	1			V
I _{GSS}	Gate-Body Leakage	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			±100	nA
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			1 25	uA
I _{D(on)}	On-State Drain Current	$V_{DS} = 5 \text{ V}, V_{Gs} = 10 \text{ V}$	25			A
rDS (on)	Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 10.4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 7.2 \text{ A}$			22 26	mΩ
g fs	Forward Tranconductance	$V_{GS} = 15 \text{ V}, I_D = 10.4 \text{ A}$		20		S
V _{SD}	Diode Forward Voltage	$I_S = 2.3 A$, $V_{GS} = 0 V$		0.7		V



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Dynamic						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
Q_g	Total Gate Charge	$V_{DS} = 30 \text{ V}$, $I_D = 10.4 \text{ A}$, $V_{GS} = 4.5 \text{ V}$		20		nC
Q_{gs}	Gate-Source Charge			5.8		nC
Q_{gd}	Gate-Drain Charge			10		nC
$t_{d(on)}$	Turn-On Delay Time	$I_{D} = 10.4 \text{ A}, R_{L} = 2.9 \Omega, \\ V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega \\ V_{DS} = 30 \text{ V}$		10		ns
$t_{\rm r}$	Rise Time			24		ns
$t_{\rm d(off)}$	Turn-Off Delay Time			67		ns
tf	Fall Time			37		ns
C _{ISS}	Input Capacitance	$V_{DS} = 15 \text{ V}$ $f = 1 \text{ MHz }, V_{GS} = 0 \text{ V}$		2086		pF
Coss	Output Capacitance			174		pF
C _{RSS}	Reverse Transfer Capacitance			160		pF

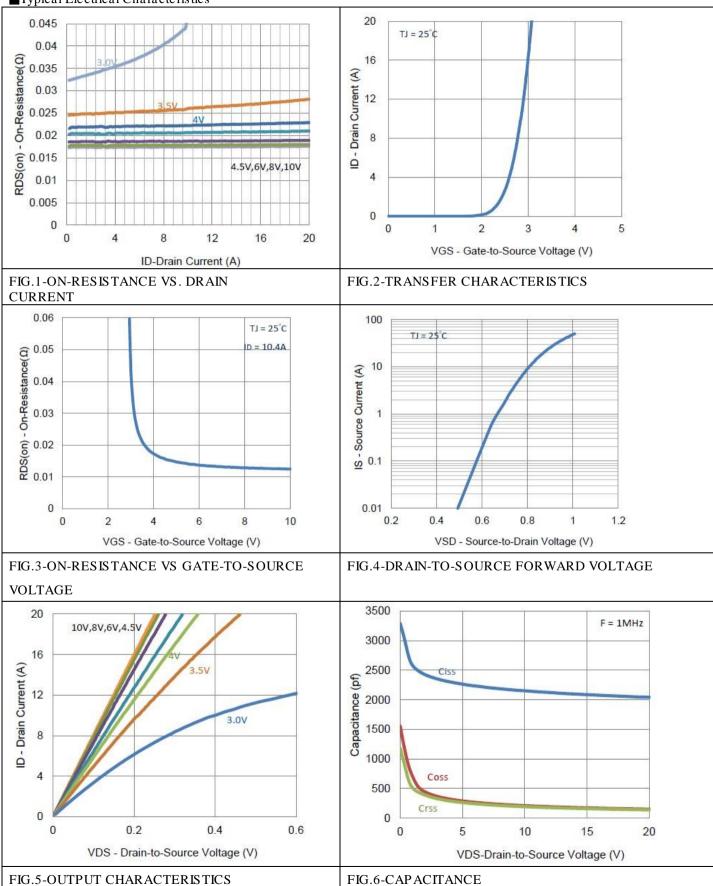
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.



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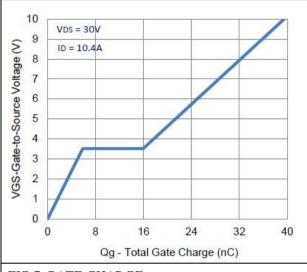






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■Typical Electrical Characteristics



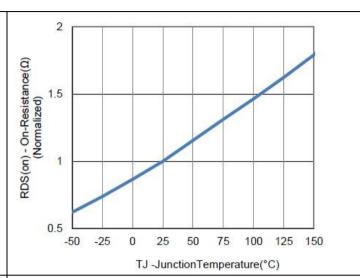


FIG.7-GATE CHARGE

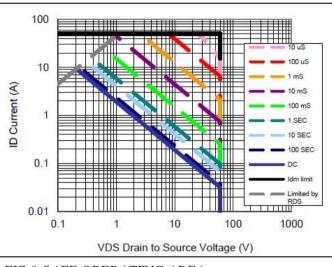


FIG.8-NORMALIZED ON-RESISTANCE VS JUNCTION TEMPERATURE

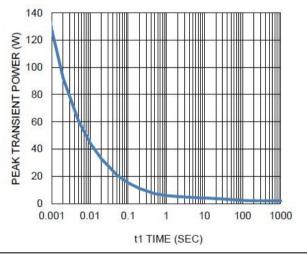
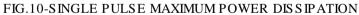


FIG.9-SAFE OPERATIING AREA



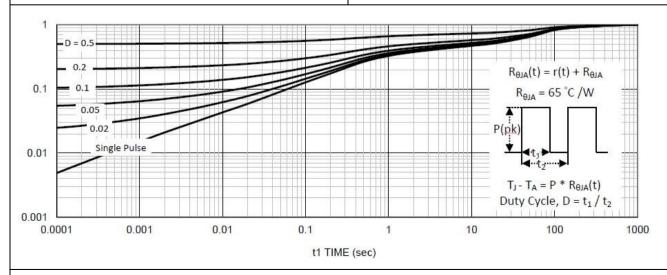


FIG.11-NORMALIZED THERMAL TRANSIENT JUNCTION TO AMBIENT



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